

4.7A, 100V, 0.540 Ohm, N-Channel Power MOSFETs

These are N-Channel enhancement mode silicon gate power field effect transistors designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. These advanced power MOSFETs are designed for use in applications such as switching regulators, switching converters, motor drivers, relay drivers and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA17441.

Ordering Information

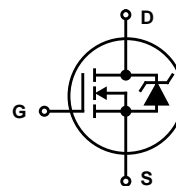
PART NUMBER	PACKAGE	BRAND
IRFU110	TO-251AA	IFU110
IRFR110	TO-252AA	IFR110

NOTE: When ordering, use the entire part number.

Features

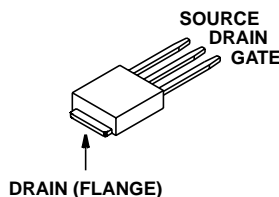
- 4.7A, 100V
- $r_{DS(ON)} = 0.540\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- 175°C Operating Temperature
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

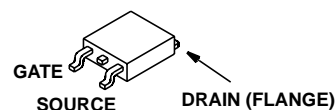


Packaging

JEDEC TO-251AA



JEDEC TO-252AA



IRFR110, IRFU110

Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

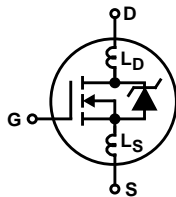
	IRFR110, IRFU110	UNITS
Drain to Source Voltage (Note 1)	V_{DS} 100	V
Drain to Gate Voltage (Note 1)	V_{DGR} 100	V
Continuous Drain Current	I_D 4.7	A
$T_C = 100^{\circ}\text{C}$	I_D 3.3	A
Pulsed Drain Current (Note 4)	I_{DM} 17	A
Gate to Source Voltage	V_{GS} ± 20	V
Maximum Power Dissipation	P_D 30	W
Linear Derating Factor	0.2	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Rating (Note 3)	E_{AS} 19	mJ
Operating and Storage Temperature	T_J, T_{STG} -55 to 175	$^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.	T_L 300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg} 260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

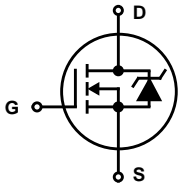
NOTE:

1. $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 10)		100	-	-	V
Gate to Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA		2	-	4	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = Rated BV _{DSS} , V _{GS} = 0V		-	-	25	μA
		V _{DS} = 0.8 x Rated BV _{DSS} , V _{GS} = 0V, T _J = 150°C		-	-	250	μA
On-State Drain Current	I _{D(ON)}	V _{DS} > I _{D(ON)} × r _{DS(ON)} MAX, V _{GS} = 10V		4.7	-	-	A
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
Drain to Source On Resistance (Note 4)	r _{DS(ON)}	I _D = 3.3A, V _{GS} = 10V (Figures 8, 9)		-	0.41	0.540	Ω
Forward Transconductance (Note 4)	g _{fs}	V _{DS} = 50V, I _{DS} = 3.3A (Figure 12)		1.3	2.0	-	S
Turn-On Delay Time	t _{d(ON)}	V _{DD} = 50V, I _D ≈ 5.6A, R _{GS} = 24Ω, R _L = 9.1Ω, V _{GS} = 10V MOSFET Switching Times are Essentially Independent of Operating Temperature		-	7.6	11	ns
Rise Time	t _r			-	24	36	ns
Turn-Off Delay Time	t _{d(OFF)}			-	14	21	ns
Fall Time	t _f			-	14	21	ns
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 10V, I _D ≈ 5.6A, V _{DS} = 0.8 x Rated BV _{DSS} , R _L = 14Ω, I _{G(REF)} = 1.5mA (Figure 14) Gate Charge is Essentially Independent of Operating Temperature		-	5.2	7.7	nC
Gate to Source Charge	Q _{gs}			-	1.5	-	nC
Gate to Drain “Miller” Charge	Q _{gd}			-	2.2	-	nC
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz (Figure 11)		-	180	-	pF
Output Capacitance	C _{OSS}			-	82	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	15	-	pF
Internal Drain Inductance	L _D	Measured from the Drain Lead, 6mm (0.25in) from Package to Center of Die	<div>Modified MOSFET Symbol Showing the Internal Devices Inductances</div> 	-	4.5	-	nH
Internal Source Inductance	L _S	Measured from The Source Lead, 6mm (0.25in) from Header to Source Bonding Pad		-	7.5	-	nH
Junction to Case	R _{θJC}			-	-	5.0	°C/W
Junction to Ambient	R _{θJA}	Free Air Operation		-	-	110	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode 	-	-	4.7	A
Pulse Source to Drain Current (Note 2)	I_{SDM}		-	-	17	A
Source to Drain Diode Voltage (Note 4)	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 4.7\text{A}$, $V_{GS} = 0\text{V}$ (Figure 13)	-	-	2.5	V
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 5.6\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	46	96	200	ns
Reverse Recovery Charge	Q_{RR}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 5.6\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	0.17	0.38	0.83	μC

NOTES:

- Repetitive rating: pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3).
- $V_{DD} = 25\text{V}$, starting $T_J = 25^{\circ}\text{C}$, $L = 1.3\text{mH}$, $R_G = 25\Omega$, peak $I_{AS} = 4.7\text{A}$.
- Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Performance Curves Unless Otherwise Specified

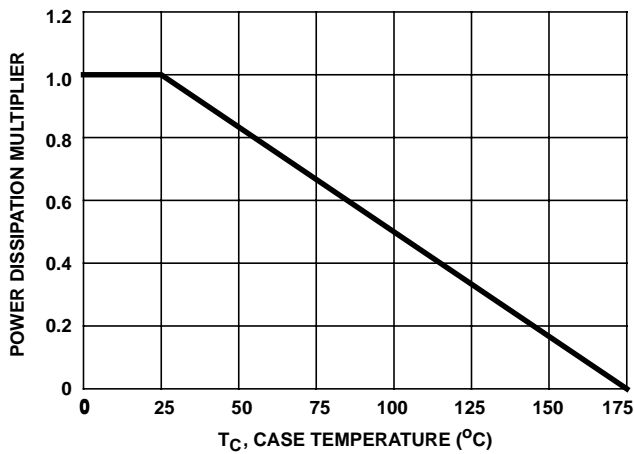


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

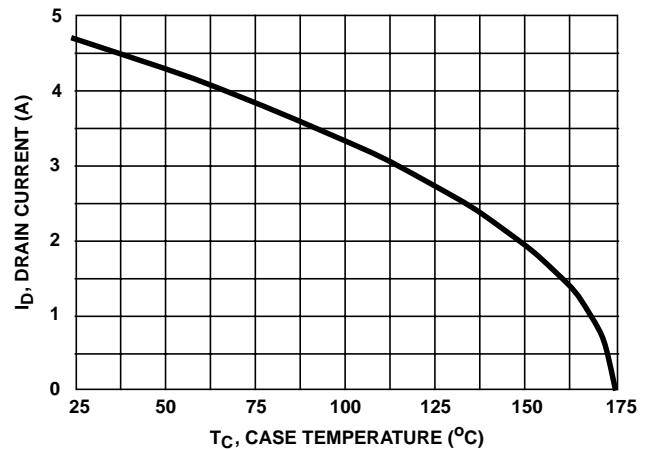


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

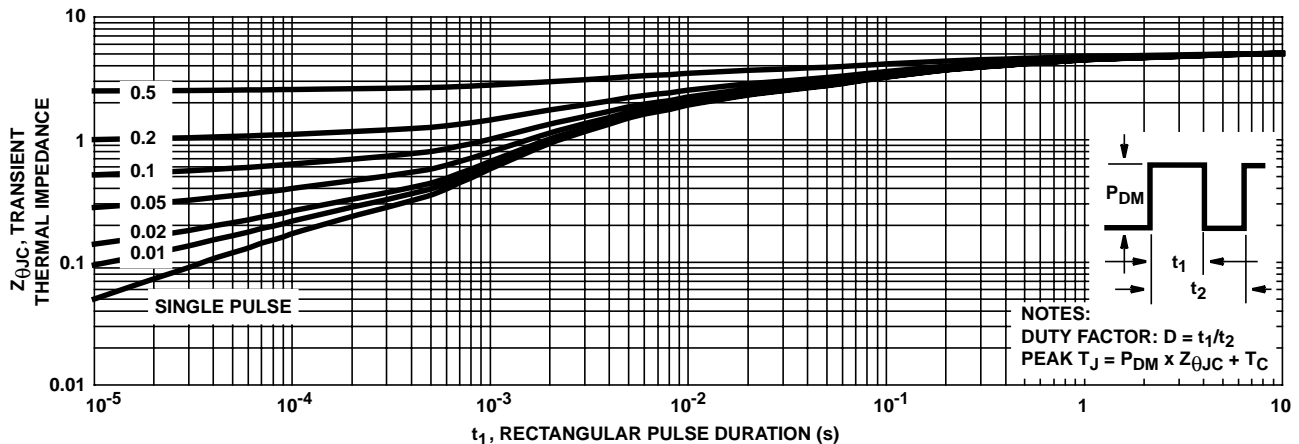


FIGURE 3. MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves Unless Otherwise Specified (Continued)

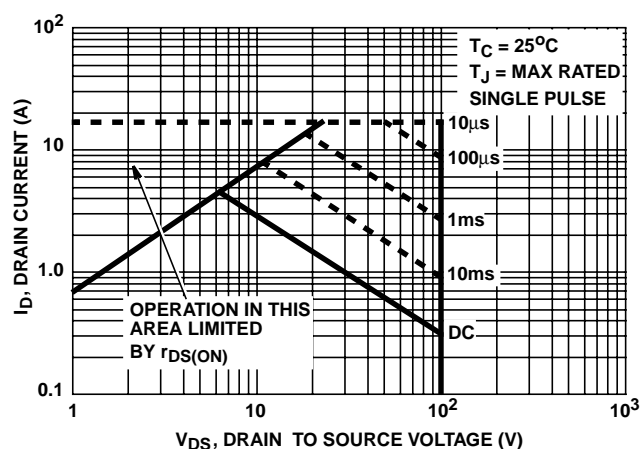


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

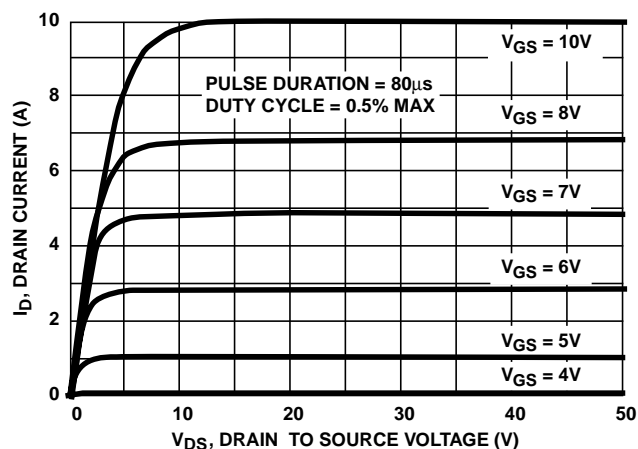


FIGURE 5. OUTPUT CHARACTERISTICS

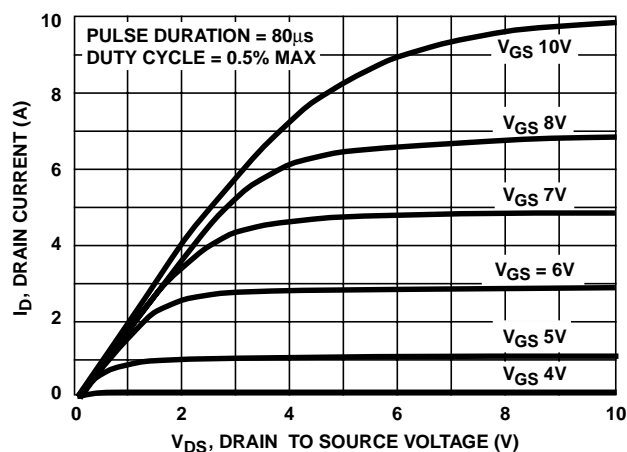


FIGURE 6. SATURATION CHARACTERISTICS

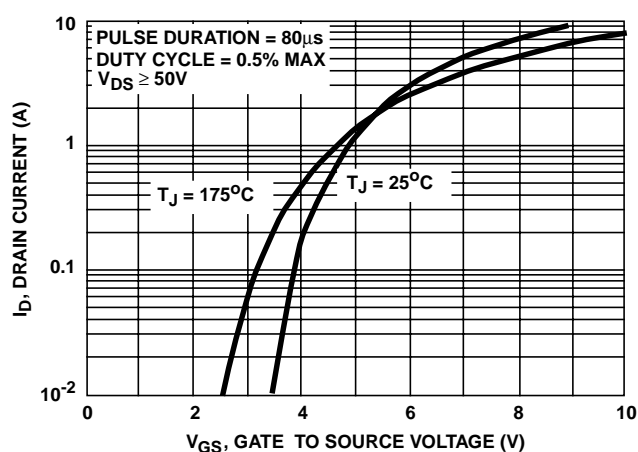


FIGURE 7. TRANSFER CHARACTERISTICS

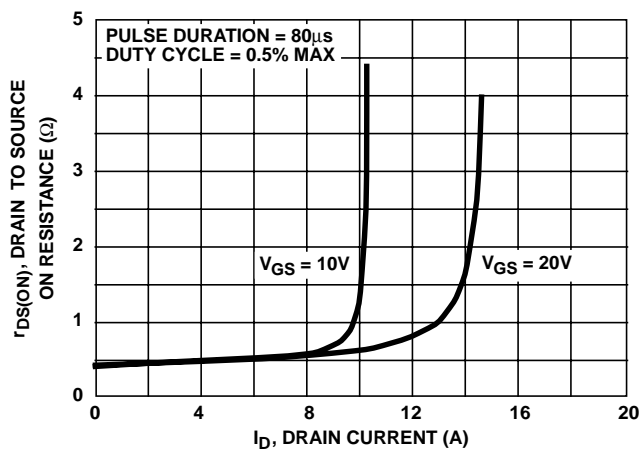


FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

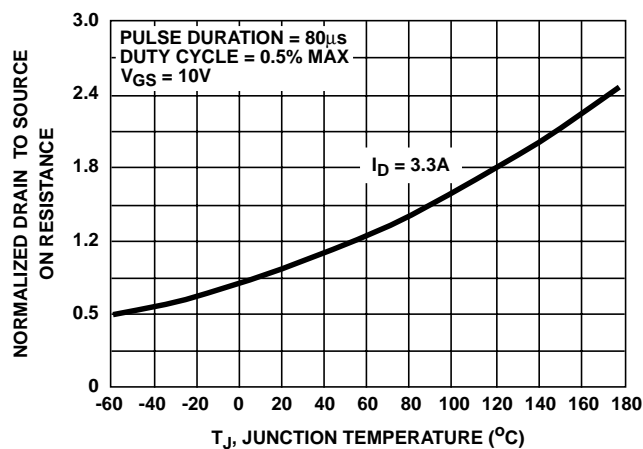


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

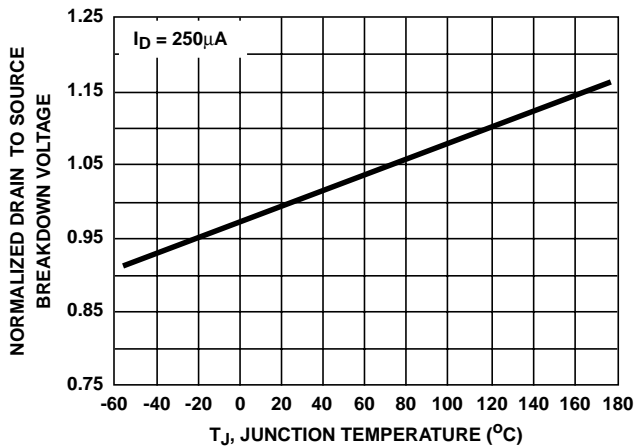


FIGURE 10. DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

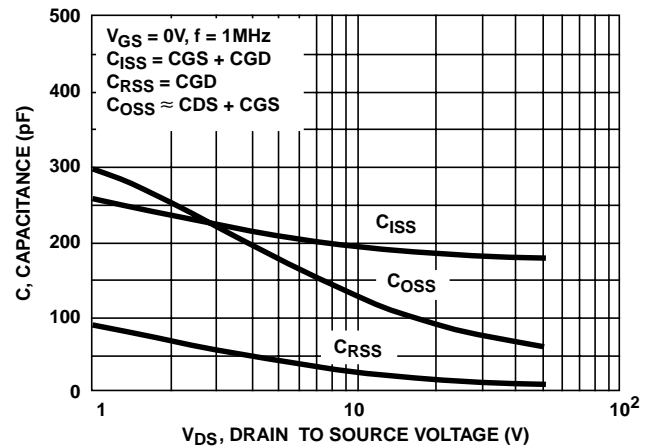


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

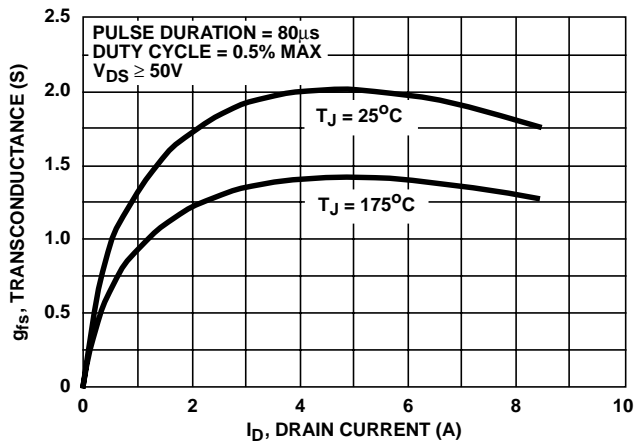


FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

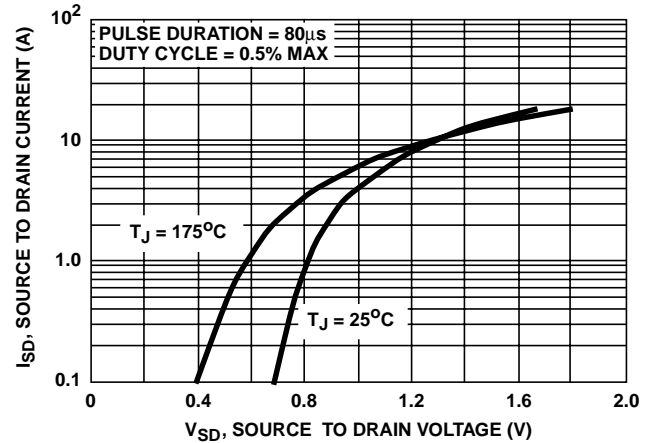


FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

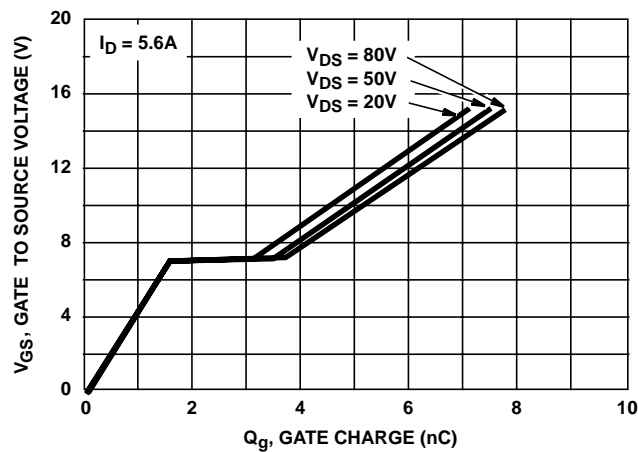


FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE

Test Circuits and Waveforms

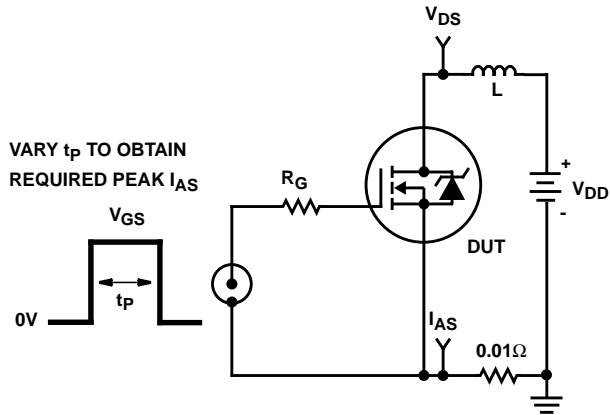


FIGURE 15. UNCLAMPED ENERGY TEST CIRCUIT

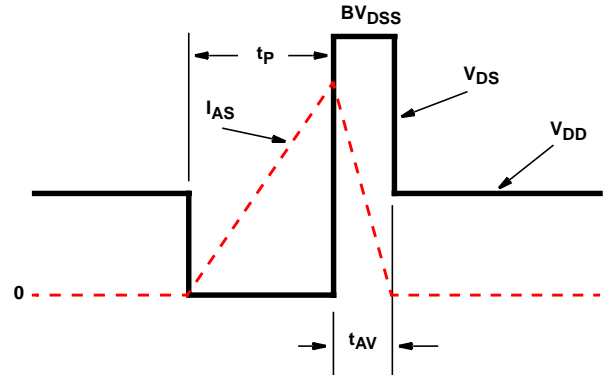


FIGURE 16. UNCLAMPED ENERGY WAVEFORMS

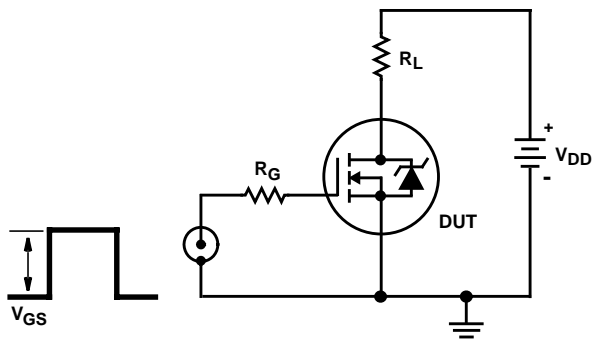


FIGURE 17. SWITCHING TIME TEST CIRCUIT

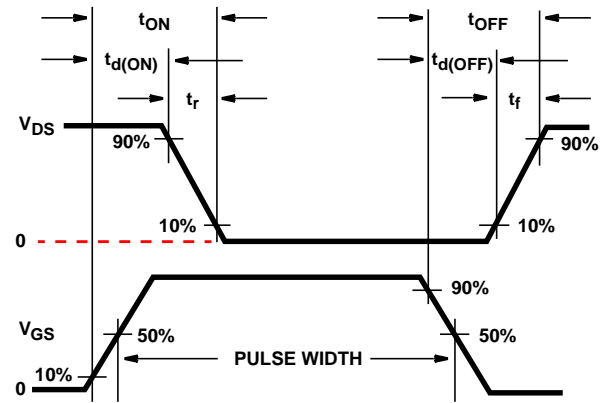


FIGURE 18. RESISTIVE SWITCHING WAVEFORMS

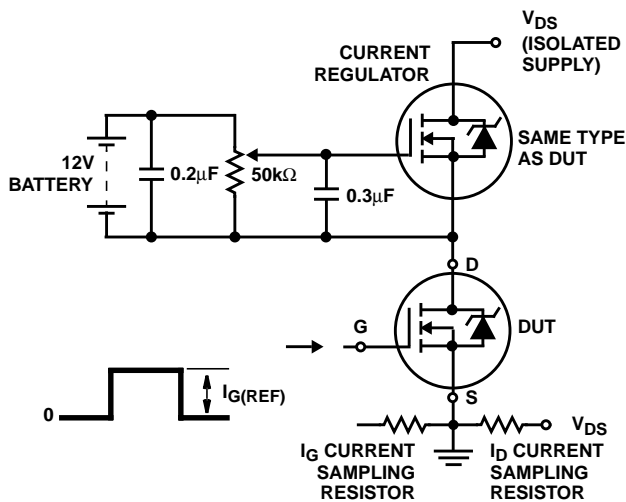


FIGURE 19. GATE CHARGE TEST CIRCUIT

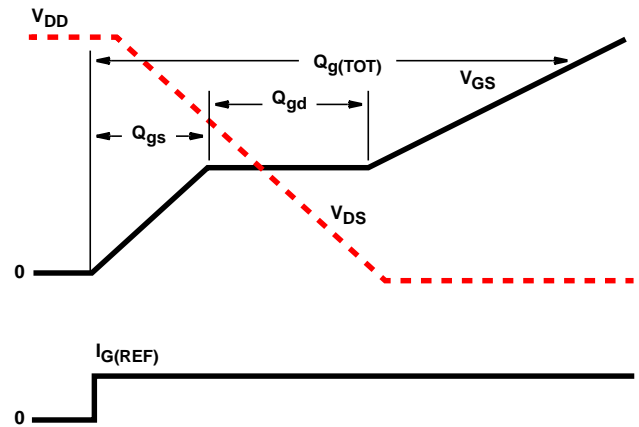


FIGURE 20. GATE CHARGE WAVEFORMS

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